

查询"2SC4641"供应商

No. 3340

SANYO

2SA1783/2SC4641

PNP/NPN Epitaxial Planar Silicon Transistors

Low-Frequency General-Purpose Amp Applications

Features

- Capable of being used in the low frequency to high frequency range.

() : 2SA1783

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Collector to Base Voltage	V_{CBO}	(-)	55	V
Collector to Emitter Voltage	V_{CEO}	(-)	50	V
Emitter to Base Voltage	V_{EB0}	(-)	6	V
Collector Current	I_C	(-)	150	mA
Collector Current (Pulse)	I_{CP}	(-)	300	mA
Base Current	I_B	(-)	30	mA
Collector Dissipation	P_C		500	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		- 55 to + 150	°C

Electrical Characteristics at $T_a = 25^\circ\text{C}$

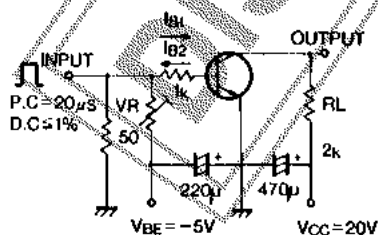
Electrical Characteristics at $T_a = 25^\circ\text{C}$			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-) 35\text{V}, I_E = 0$			$(-) 0.1$	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-) 4\text{V}, I_C = 0$			$(-) 0.1$	μA
DC Current Gain	h_{FE}	$V_{CE} = (-) 6\text{V}, I_C = (-) 1\text{mA}$	140		560	
Gain-Bandwidth Product	f_T	$V_{CE} = (-) 6\text{V}, I_C = (-) 10\text{mA}$		200 (180)		MHz
Output Capacitance	c_{ob}	$V_{CB} = (-) 6\text{V}, f = 1\text{MHz}$		2.2 (3.5)		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-) 50\text{mA}, I_B = (-) 5\text{mA}$		0.08 (-0.11)	$(-) 0.4$	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-) 50\text{mA}, I_B = (-) 5\text{mA}$		(-) 0.8	$(-) 1.0$	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10\mu\text{A}, I_E = 0$	(-) 55			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-) 1\text{mA}, R_{BE} = \infty$	(-) 50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-) 10\mu\text{A}, I_C = 0$	(-) 6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		0.15		μs
Storage Time	t_{stg}	"		0.75 (0.60)		μs
Fall Time	t_f	"		0.20		μs

*: The 2SA1783/2SC4641 are classified by 1mA h_{FE} as follows:

140	S	280	200	T	400	280	U	560
-----	---	-----	-----	---	-----	-----	---	-----

hFE rank: S, T, U

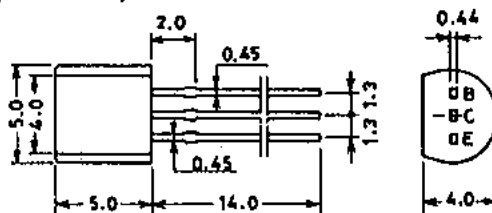
Switching Time Test Circuit

Unit(Resistance : Ω , Capacitance : F)
$$10I_{B1} = -10I_{B2} = I_C = 10\text{ mA}$$

(For PNP, the polarity is reversed.)

Case Outline 2003A

(unit : mm)



JEDEC: TO-92

EIAJ : SC-43

SANYO: NP

B: Base

C: Collector

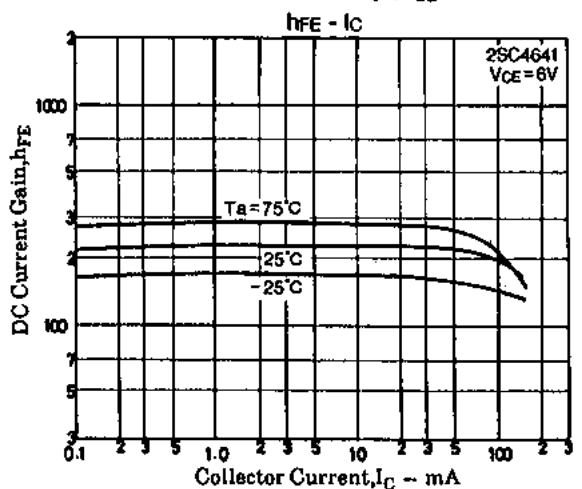
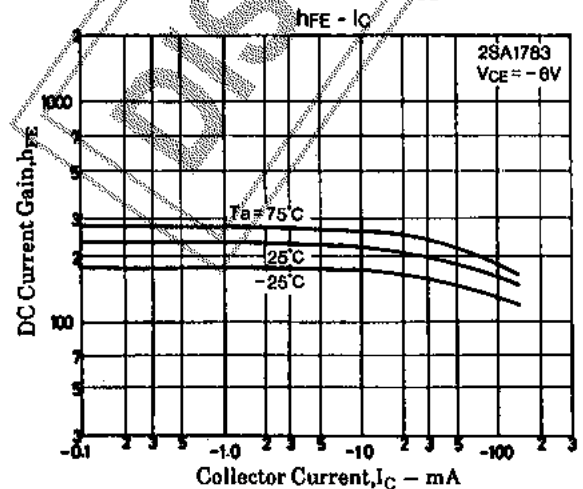
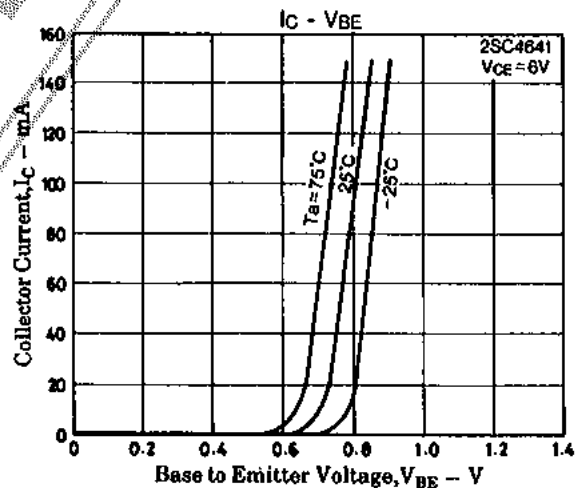
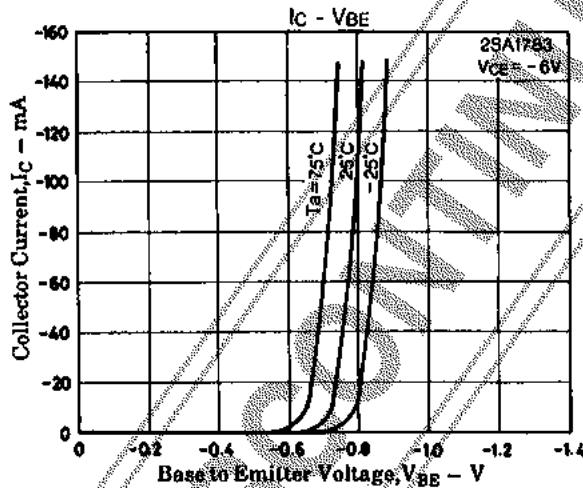
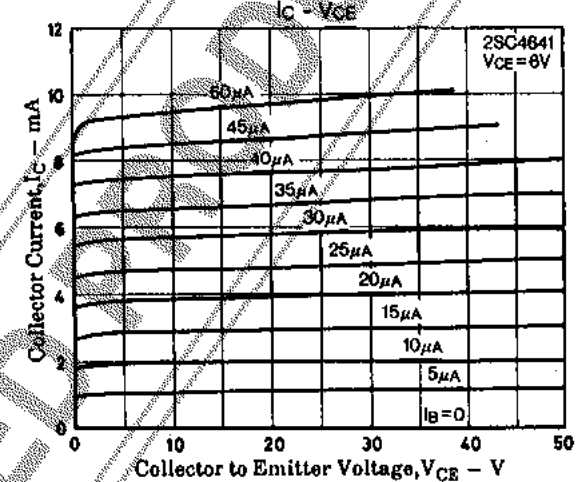
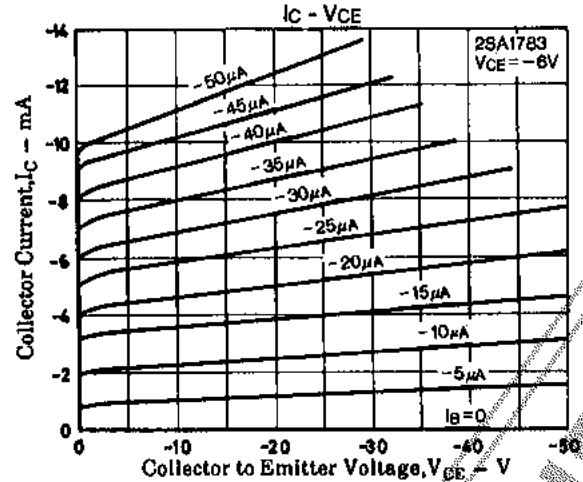
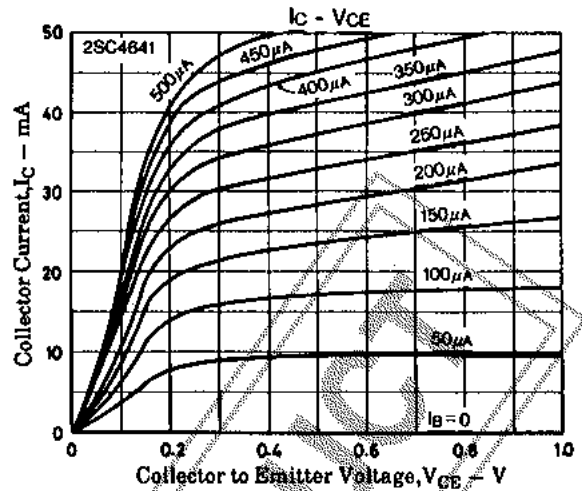
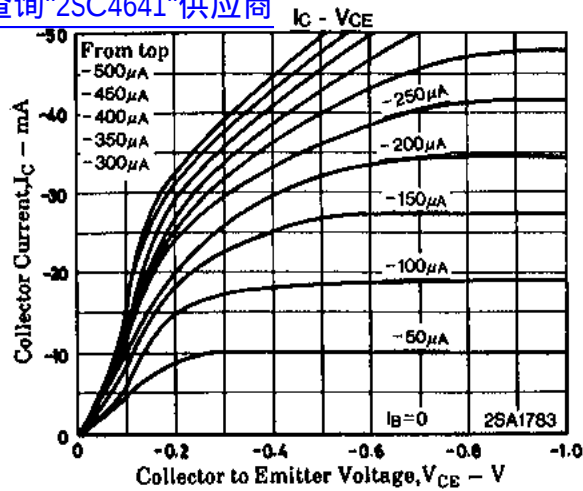
E: Emitter

Specifications and information herein are subject to change without notice.

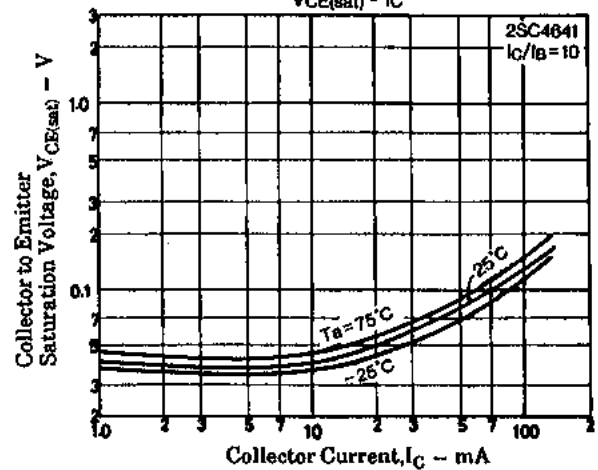
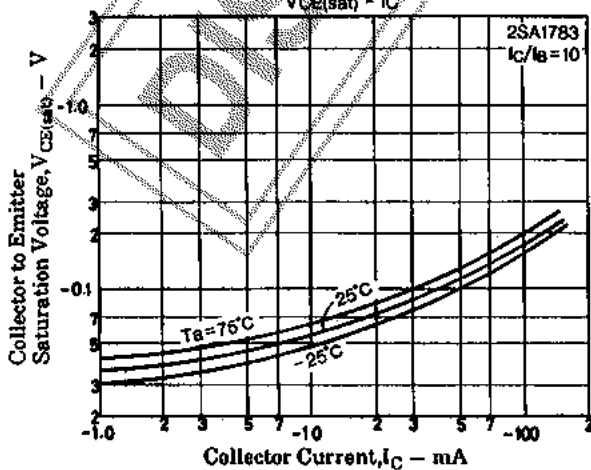
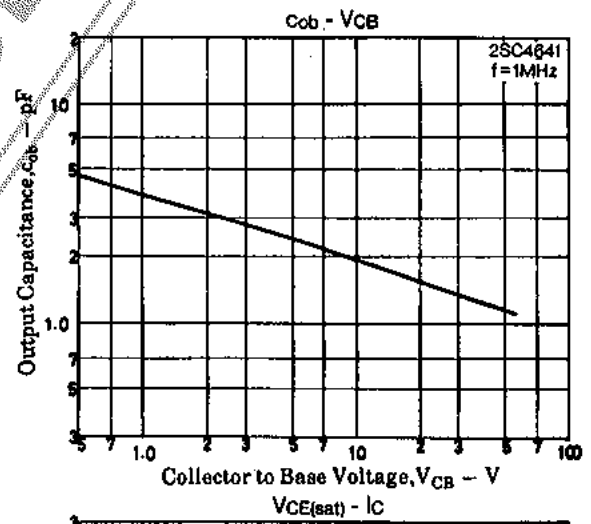
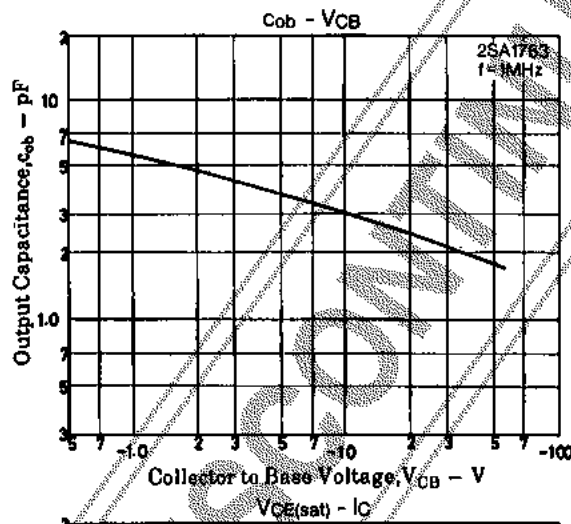
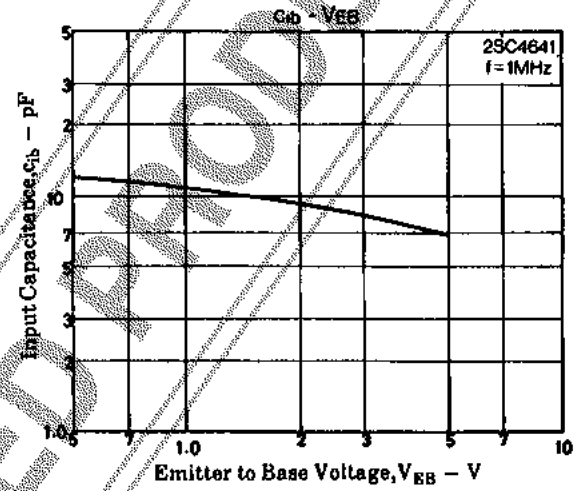
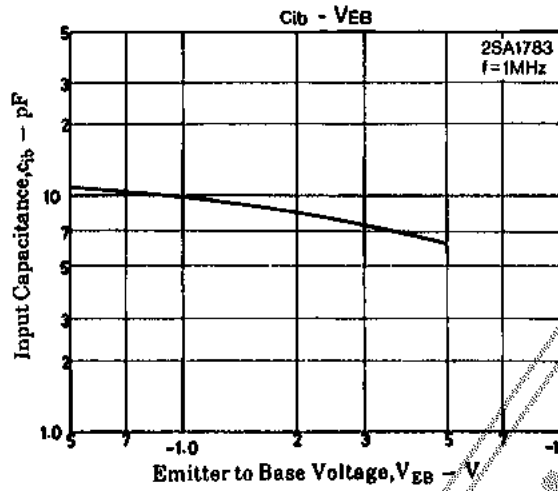
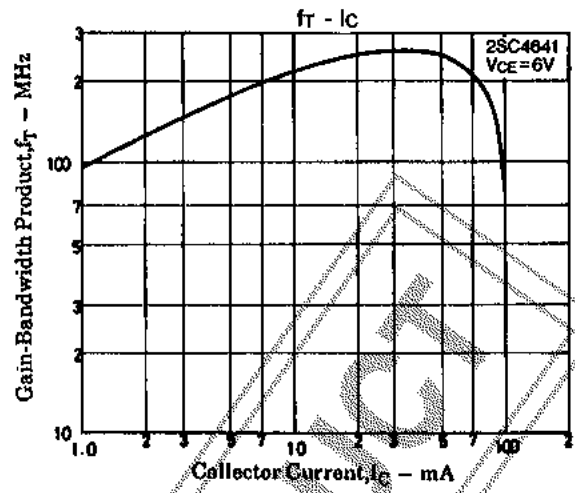
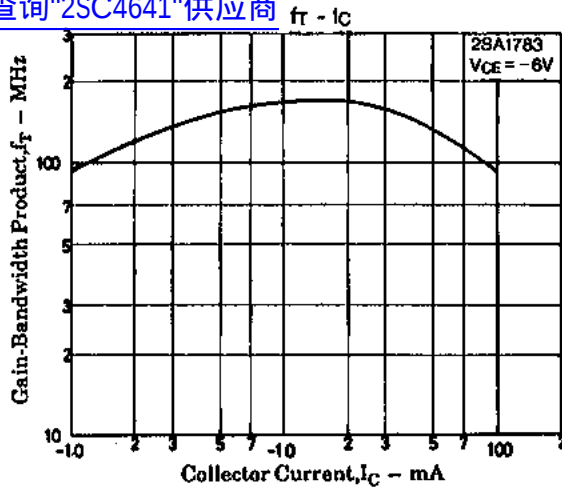
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

3230MO,TS No.3340-1/4



查询"2SC4641"供应商



查询"2SC4641"供应商

